

Philippe Godignon

List of Publications by Year in descending order

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186
papers

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188
times ranked

8426
citing authors

#	ARTICLE	IF	CITATIONS
1	Carrier Concentration Analysis in 1.2 kV SiC Schottky Diodes Under Current Crowding. IEEE Electron Device Letters, 2022, 43, 938-941.	2.2	4
2	Reliability and Robustness Tests for Next-Generation High-Voltage SiC MOSFETs. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2021, 9, 4320-4329.	3.7	5
3	60-700 K CTAT and PTAT Temperature Sensors with 4H-SiC Schottky Diodes. Sensors, 2021, 21, 942.	2.1	12
4	Deep level study of chlorine-based dry etched $\text{AlGaInGaAs}/\text{GaAs}/\text{Ga}_2\text{O}_3$. Journal of Applied Physics, 2021, 130, .1.1		8
5	Bidirectional Modulation of Neuronal Cells Electrical and Mechanical Properties Through Pristine and Functionalized Graphene Substrates. Frontiers in Neuroscience, 2021, 15, 811348.	1.4	3
6	Electronic interface and charge carrier density in epitaxial graphene on silicon carbide. A review on metal-graphene contacts and electrical gating. APL Materials, 2020, 8, .	2.2	6
7	IBIC analysis of SiC detectors developed for fusion applications. Radiation Physics and Chemistry, 2020, 177, 109100.	1.4	8
8	Simulation-Based Analysis of Thermo-Mechanical Constraints in Packages for Diamond Power Devices. , 2020, , .		3
9	Current Crowding Study by IIR-LD in a 1.2 kV SiC Schottky Diode. , 2020, , .		0
10	Electron, Neutron, and Proton Irradiation Effects on SiC Radiation Detectors. IEEE Transactions on Nuclear Science, 2020, 67, 2481-2489.	1.2	35
11	Analysis of SiC Schottky diodes after thermal vacuum test by means of lock-in infrared thermography. , 2020, , .		1
12	An Investigation into the Dynamic Behavior of 3.3kV MOSFETs Body Diode. Materials Science Forum, 2019, 963, 621-624.	0.3	0
13	Comparative study of boron doped gate oxide impact on 4H and 6H-SiC n-MOSFETs. Materials Science in Semiconductor Processing, 2019, 93, 357-359.	1.9	6
14	Neural interfaces based on flexible graphene transistors: A new tool for electrophysiology. , 2019, , .		1
15	Dynamic Characterization and Robustness Test of High Voltage SiC MOSFETs. Materials Science Forum, 2019, 963, 768-772.	0.3	2
16	Delta Reference, the Latest High Temperature Compensated Voltage Reference Concept. , 2019, , .		0
17	Latest Concept to Generate Temperature Compensated Voltage Reference. , 2019, , .		0
18	High-resolution mapping of infraslow cortical brain activity enabled by graphene microtransistors. Nature Materials, 2019, 18, 280-288.	13.3	121

#	ARTICLE	IF	CITATIONS
19	Four-quadrant silicon and silicon carbide photodiodes for beam position monitor applications: electrical characterization and electron irradiation effects. Journal of Instrumentation, 2018, 13, C01045-C01045.	0.5	8
20	Advanced processing for mobility improvement in 4H-SiC MOSFETs: A review. Materials Science in Semiconductor Processing, 2018, 78, 22-31.	1.9	80
21	Flexible Graphene Solution-Gated Field-Effect Transistors: Efficient Transducers for Micro-Electrocorticography. Advanced Functional Materials, 2018, 28, 1703976.	7.8	97
22	Advantages and Challenges of Plasma Immersion Ion Implantation for Power Devices Manufacturing on Si, SiC and GaN using PULSION [®] Tool. , 2018, , .		0
23	Surface Recombination Evaluation in Bipolar Junction Transistors by Combined Electro-Optical Method. , 2018, , .		0
24	Gate Oxide Electrical Stability of p-type Diamond MOS Capacitors. IEEE Transactions on Electron Devices, 2018, 65, 3361-3364.	1.6	12
25	Long term high temperature reverse bias (HTRB) test on high voltage SiC-JBS-diodes. , 2018, , .		3
26	Assessing Radiation Hardness of SiC MOS Structures. , 2018, , .		1
27	10 μ m-thick four-quadrant transmissive silicon photodiodes for beam position monitor application: electrical characterization and gamma irradiation effects. Journal of Instrumentation, 2017, 12, C01004-C01004.	0.5	6
28	Al-implanted on-axis 4H-SiC MOSFETs. Semiconductor Science and Technology, 2017, 32, 035006.	1.0	9
29	Planar edge terminations for high voltage 4H-SiC power MOSFETs. Semiconductor Science and Technology, 2017, 32, 035007.	1.0	6
30	Experimental investigation of SiC 6.5kV JBS diodes safe operating area. , 2017, , .		5
31	Prototyping and Characterization of 1.2KV SiC Schottky Diodes for TWTA Application: The Challenge to Meet the User Specification. E3S Web of Conferences, 2017, 16, 12005.	0.2	1
32	Impact of boron diffusion on oxynitrided gate oxides in 4H-SiC metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2017, 111, .	1.5	17
33	Impact of Thermal Treatments in Crystalline Reconstruction and Electrical Properties of Diamond Ohmic Contacts Created by Boron Ion Implantation. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1700230.	0.8	7
34	High channel mobility in 4H-SiC N-MOSFET using N ₂ O oxidation combined with Boron diffusion treatment. , 2017, , .		0
35	High-Voltage 4H-SiC Power MOSFETs With Boron-Doped Gate Oxide. IEEE Transactions on Industrial Electronics, 2017, 64, 8962-8970.	5.2	19
36	Impact of layout on the surge current robustness of 1.2 KV SiC diodes. , 2017, , .		4

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37	New trends in high voltage MOSFET based on wide band gap materials. , 2017, , .		9
38	Power cycling and surge current tester for SiC power devices. , 2016, , .		5
39	Power cycling analysis method for high-voltage SiC diodes. Microelectronics Reliability, 2016, 64, 429-433.	0.9	8
40	4.5kV SiC MOSFET with boron doped gate dielectric. , 2016, , .		8
41	A model to non-uniform Ni Schottky contact on SiC annealed at elevated temperatures. Applied Physics Letters, 2015, 106, .	1.5	25
42	Design of voltage comparator integrated circuit with normally-on MESFETs on 4H-SiC semiconductor. , 2015, , .		2
43	An electrostatic-discharge-protection solution for Silicon-Carbide MESFET. , 2015, , .		1
44	High-voltage SiC devices: Diodes and MOSFETs. , 2015, , .		9
45	Experimental analysis of planar edge terminations for high voltage 4H-SiC devices. , 2015, , .		4
46	SiC Integrated Circuit Control Electronics for High-Temperature Operation. IEEE Transactions on Industrial Electronics, 2015, 62, 3182-3191.	5.2	52
47	Failure analysis of ESD-stressed SiC MESFET. Microelectronics Reliability, 2015, 55, 1542-1548.	0.9	4
48	Local non invasive study of SiC diodes with abnormal electrical behavior. Solid-State Electronics, 2015, 113, 35-41.	0.8	6
49	Tuning the Terrace and Step Stability of 6H-SiC (0001) for Graphene Film Deposition. Materials Science Forum, 2015, 821-823, 953-956.	0.3	0
50	Quantum Hall effect of self-organized graphene monolayers on the C-face of 6H-SiC. Journal Physics D: Applied Physics, 2014, 47, 094009.	1.3	5
51	A positive impact of low proton irradiation energy on oxynitride gate 4H-SiC MOSFETs. , 2014, , .		1
52	Study of surface weak spots on SiC Schottky Diodes under specific operating regimes by Infrared Lock-in sensing. , 2014, , .		0
53	Monolithic Integration of Power MESFET for High Temperature SiC Integrated Circuits. Materials Science Forum, 2014, 778-780, 891-894.	0.3	3
54	Demonstration of temperature compensated voltage reference integrated circuit designed with 4H-SiC MESFETs. , 2014, , .		6

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55	A Survey of Wide Bandgap Power Semiconductor Devices. IEEE Transactions on Power Electronics, 2014, 29, 2155-2163.	5.4	1,700
56	Structural analysis of SiC Schottky diodes failure mechanism under current overload. Journal Physics D: Applied Physics, 2014, 47, 055102.	1.3	5
57	Thermomechanical Assessment of Die-Attach Materials for Wide Bandgap Semiconductor Devices and Harsh Environment Applications. IEEE Transactions on Power Electronics, 2014, 29, 2261-2271.	5.4	87
58	Temperature effects on the ruggedness of SiC Schottky diodes under surge current. Microelectronics Reliability, 2014, 54, 2207-2212.	0.9	6
59	Small signal thermal analysis of local multibarrier behaviour in SiC Schottky diodes. Journal Physics D: Applied Physics, 2014, 47, 385101.	1.3	7
60	5ÂMeV Proton and 15ÂMeV Electron Radiation Effects Study on 4H-SiC nMOSFET Electrical Parameters. IEEE Transactions on Nuclear Science, 2014, 61, 1732-1738.	1.2	18
61	Analysis of an ESD failure mechanism on a SiC MESFET. Microelectronics Reliability, 2014, 54, 2217-2221.	0.9	4
62	Monolithically Integrated Temperature Sensor in Silicon Carbide Power MOSFETs. IEEE Transactions on Power Electronics, 2014, 29, 4970-4977.	5.4	33
63	Wide Band Gap power semiconductor devices. , 2013, , .		19
64	Mercury detection at microfabricated pyrolyzed photoresist film (PPF) disk electrodes. Sensors and Actuators B: Chemical, 2013, 186, 293-299.	4.0	13
65	Multi-walled carbon nanotube based multi-electrode arrays for the detection of the emergent activity in the cortical network. Microelectronic Engineering, 2013, 112, 14-20.	1.1	4
66	Membraneless glucose/O ₂ microfluidic enzymatic biofuel cell using pyrolyzed photoresist film electrodes. Lab on A Chip, 2013, 13, 2972.	3.1	68
67	Thermal Behavior of SiC Power Diodes. ECS Transactions, 2013, 50, 399-410.	0.3	1
68	Monolithic Integration of High Temperature Silicon Carbide Integrated Circuits. ECS Transactions, 2013, 58, 375-388.	0.3	3
69	4H-SiC MESFET specially designed and fabricated for high temperature integrated circuits. , 2013, , .		10
70	5 MeV proton and 15 MeV electron radiation effects study on 4H-SiC nMOSFET electrical parameters. , 2013, , .		3
71	High temperature-low temperature coefficient analog voltage reference integrated circuit implemented with SiC MESFETs. , 2013, , .		9
72	Effect of the Growth Conditions on the Properties of Nitrided Oxides Grown by RTP for 4H-SiC p-Channel MOSFETs Fabrication. Journal of the Electrochemical Society, 2012, 159, H516-H521.	1.3	1

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73	Quantum Hall effect in bottom-gated epitaxial graphene grown on the C-face of SiC. Applied Physics Letters, 2012, 100, .	1.5	20
74	SiC Schottky Diode surge current analysis and application design using behavioral SPICE models. , 2012, , .		8
75	SiC-based MIS gas sensor for high water vapor environments. Sensors and Actuators B: Chemical, 2012, 175, 60-66.	4.0	17
76	A HfO ₂ /Al ₂ O ₃ based 800V/300A Au-free AlGa _N /Ga _N -on-Si HEMT technology. , 2012, , .		9
77	High Voltage SiC Schottky Diodes in Rectifiers for X-Ray Generators. Materials Science Forum, 2012, 717-720, 1245-1248.	0.3	3
78	High voltage low Ron in-situ SiN/Al _{0.35} Ga _{0.65} /Ga _N -on-Si power HEMTs operation up to 300°C. , 2012, , .		0
79	Enhanced power cycling capability of SiC Schottky diodes using press pack contacts. Microelectronics Reliability, 2012, 52, 2250-2255.	0.9	18
80	Wafer scale and reliability investigation of thin HfO ₂ -AlGa _N /Ga _N MIS-HEMTs. Microelectronics Reliability, 2012, 52, 2220-2223.	0.9	11
81	Real time protein recognition in a liquid-gated carbon nanotube field-effect transistor modified with aptamers. Nanoscale, 2012, 4, 5917.	2.8	23
82	Wide Band Gap Semiconductor Devices for Power Electronics. Automatika, 2012, 53, 107-116.	1.2	22
83	Optical nano-imaging of gate-tunable graphene plasmons. Nature, 2012, 487, 77-81.	13.7	1,820
84	A simple approach for DNA detection on carbon nanotube microelectrode arrays. Sensors and Actuators B: Chemical, 2012, 162, 120-127.	4.0	13
85	Comparison between mesa isolation and p ⁺ implantation isolation for 4H-SiC MESFET transistors. , 2011, , .		8
86	SiC-Based MIS Gas Sensor for High Water Vapor Environments. Procedia Engineering, 2011, 25, 1321-1324.	1.2	0
87	SiC Schottky Diodes for Harsh Environment Space Applications. IEEE Transactions on Industrial Electronics, 2011, 58, 2582-2590.	5.2	83
88	Micro-Raman and micro-transmission imaging of epitaxial graphene grown on the Si and C faces of 6H-SiC. Nanoscale Research Letters, 2011, 6, 478.	3.1	19
89	Study of 4H-SiC JBS Diodes Fabricated with Tungsten Schottky Barrier. Journal of Electronic Materials, 2011, 40, 2355-2362.	1.0	16
90	Observation and characterization of near-interface oxide traps in 3C-SiC MOS structures by quasi-static C-V method. Solid-State Electronics, 2011, 63, 70-75.	0.8	2

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91	Rapid Growth of Oxide Films on SiC by Photo-Assisted Mechanism. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, G42.	2.2	2
92	Nitrided Gate Oxide Formed by Rapid Thermal Processing for 4H-SiC MOSFETs. <i>ECS Transactions</i> , 2011, 35, 157-164.	0.3	2
93	Interfacial Properties of Oxides Grown on 3C-SiC by Rapid Thermal Processing. <i>Journal of the Electrochemical Society</i> , 2011, 158, G13.	1.3	10
94	Fabrication of PPF Electrodes by a Rapid Thermal Process. <i>Journal of the Electrochemical Society</i> , 2011, 158, H63.	1.3	21
95	Epitaxial Graphene Growth on β -SiC: Probing the Effect of Surface Orientation. <i>Nanoscience and Nanotechnology Letters</i> , 2011, 3, 49-54.	0.4	9
96	Low-cost trench isolation technique for reverse blocking IGBT using boron nitride doping wafers. <i>Microelectronic Engineering</i> , 2010, 87, 2323-2327.	1.1	7
97	Massive manufacture and characterization of single-walled carbon nanotube field effect transistors. <i>Microelectronic Engineering</i> , 2010, 87, 1554-1556.	1.1	21
98	Interfacial properties of AlN and oxidized AlN on Si. <i>Surface Science</i> , 2010, 604, 63-67.	0.8	11
99	Deposited Thin SiO ₂ for Gate Oxide on n-Type and p-Type GaN. <i>Journal of the Electrochemical Society</i> , 2010, 157, H1008.	1.3	20
100	Growth of monolayer graphene on 8° off-axis 4H-SiC (0001) substrates with application to quantum transport devices. <i>Applied Physics Letters</i> , 2010, 97, 093107.	1.5	21
101	Batch wafer scale fabrication of passivated carbon nanotube transistors for electrochemical sensing applications. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2010, 28, C6P1-C6P5.	0.6	7
102	Integration of HfO ₂ on Si/SiC heterojunctions for the gate architecture of SiC power devices. <i>Applied Physics Letters</i> , 2010, 97, 013506.	1.5	8
103	Probing the electrical anisotropy of multilayer graphene on the Si face of 6H-SiC. <i>Physical Review B</i> , 2010, 82, .	1.1	29
104	Effects of Photons on 4H-SiC Rapid Thermal Oxidation Using Nitrous Oxide Gas. <i>Journal of the Electrochemical Society</i> , 2010, 157, G136.	1.3	19
105	Rapid Thermal Oxynitridation and Hydrogenation of 3C-SiC-Si using N ₂ O and H ₂ Ambient. , 2010, , .		0
106	Current status of self-organized epitaxial graphene ribbons on the C face of 6H-SiC substrates. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 374011.	1.3	29
107	3C-SiC films on insulated substrates for high-temperature electrostatic-based resonators. <i>Journal of Micromechanics and Microengineering</i> , 2010, 20, 115007.	1.5	5
108	High temperature SiC Schottky diodes with stable operation for space application. , 2010, , .		4

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109	Design of logic gates for high temperature and harsh radiation environment made of 4H-SiC MESFET. , 2010, , .		13
110	A test vehicle and a two step procedure to evaluate a massive number of single-walled carbon nanotube field effect transistors. , 2010, , .		1
111	GaN transistor characteristics at elevated temperatures. Journal of Applied Physics, 2009, 106, .	1.1	67
112	Benefit of H ₂ surface pretreatment for 4H-SiC oxynitridation using N ₂ O and rapid thermal processing steps. Applied Physics Letters, 2009, 94, .	1.5	24
113	GaN metal-oxide-semiconductor field-effect transistor inversion channel mobility modeling. Journal of Applied Physics, 2009, 105, .	1.1	40
114	Accelerated test for reliability analysis of SiC diodes. Power Semiconductor Devices & IC's, 2009 ISPSD 2009 21st International Symposium on, 2009, , .	0.0	10
115	Physical modelling of large area 4H-SiC PiN diodes. , 2009, , .		3
116	Novel structures of 3.3kV 4H-SiC BJTs to reduce the Stacking Faults expansion. Power Semiconductor Devices & IC's, 2009 ISPSD 2009 21st International Symposium on, 2009, , .	0.0	0
117	Nanostructuring of epitaxial graphene layers on SiC by means of field-induced atomic force microscopy modification. Journal of Vacuum Science & Technology B, 2009, 27, 3149-3152.	1.3	15
118	Low loss, large area 4.5 kV 4H-SiC PIN diodes with reduced forward voltage drift. Semiconductor Science and Technology, 2009, 24, 095004.	1.0	16
119	Effects of cap layer on ohmic Ti/Al contacts to Si ⁺ implanted GaN. Applied Surface Science, 2009, 255, 6057-6060.	3.1	30
120	Vertically aligned multi-walled carbon nanotube growth on platinum electrodes for bio-impedance applications. Microelectronic Engineering, 2009, 86, 806-808.	1.1	19
121	Epitaxial aluminium nitride on patterned silicon. Materials Science in Semiconductor Processing, 2009, 12, 31-33.	1.9	2
122	Highly sensitive strained AlN on Si(111) resonators. Sensors and Actuators A: Physical, 2009, 150, 64-68.	2.0	11
123	Anisotropic growth of long isolated graphene ribbons on the C face of graphite-capped $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mn} \rangle 6 \langle \text{mml:mn} \rangle \langle \text{mml:mi} \rangle H \langle \text{mml:mi} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:math} \rangle$ -SiC. Physical Review B, 2009, 80, .	1.1	88
124	Accelerated Life Test for SiC Schottky Blocking Diodes in High-Temperature Environment. IEEE Transactions on Device and Materials Reliability, 2009, 9, 557-562.	1.5	19
125	Ohmic Contacts to implanted GaN. , 2009, , .		1
126	Comparaison de diodes SiC-4H Schottky et bipolaires 3 kV-20 A. Revue Internationale De Génie Électrique, 2009, 12, 225-236.	0.0	0

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127	Interfacial properties of thermally oxidized Ta ₂ Si on Si. Surface and Interface Analysis, 2008, 40, 1164-1167.	0.8	2
128	CVD oriented growth of carbon nanotubes using AlPO ₄₋₅ and L type zeolites. Microelectronic Engineering, 2008, 85, 1202-1205.	1.1	9
129	Fabrication of monocrystalline 3C-SiC resonators for MHz frequency sensors applications. Sensors and Actuators B: Chemical, 2008, 133, 276-280.	4.0	28
130	Characterization at the nanometer scale of local electron beam irradiation of CNT based devices. Microelectronic Engineering, 2008, 85, 1413-1416.	1.1	9
131	SiC MOSFETs with thermally oxidized Ta ₂ Si stacked on SiO ₂ as high-k gate insulator. Microelectronic Engineering, 2008, 85, 704-709.	1.1	10
132	Behaviour of 1.2 kV SiC JBS diodes under repetitive high power stress. Microelectronics Reliability, 2008, 48, 1444-1448.	0.9	17
133	Bipolar Conduction Impact on Electrical Characteristics and Reliability of 1.2- and 3.5-kV 4H-SiC JBS Diodes. IEEE Transactions on Electron Devices, 2008, 55, 1847-1856.	1.6	27
134	Selective epitaxial growth of graphene on SiC. Applied Physics Letters, 2008, 93, 123503.	1.5	43
135	The effect of the temperature on the Bipolar Degradation of 3.3 kV 4H-SiC PiN diodes. , 2008, , .		9
136	Electrical performance at high temperature and surge current of 1.2 kV power rectifiers: Comparison between Si PiN, 4H-SiC Schottky and JBS diodes. , 2008, , .		7
137	Schottky versus bipolar 3.3 kV SiC diodes. Semiconductor Science and Technology, 2008, 23, 125004.	1.0	26
138	Early stage formation of graphene on the C face of 6H-SiC. Applied Physics Letters, 2008, 93, .	1.5	39
139	Comparison between 3.3kV 4H-SiC Schottky and bipolar diodes. , 2008, , .		0
140	1.2 kV Rectifiers Thermal Behaviour: comparison between Si PiN, 4H-SiC Schottky and JBS diodes. , 2007, , .		10
141	Improvement of 4H-SiC selective epitaxial growth by VLS mechanism using Al and Ge-based melts. Diamond and Related Materials, 2007, 16, 37-45.	1.8	10
142	High temperature behaviour of 3.5 kV 4H-SiC JBS diodes. , 2007, , .		5
143	Validation of Dynamic Thermal Simulations of Power Assemblies Using a Thermal Test Chip. , 2007, , .		5
144	Local growth of carbon nanotubes by thermal chemical vapor deposition from iron based precursor nanoparticles. , 2007, , .		3

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145	Coupled electro-thermal simulation of a DC/DC converter. <i>Microelectronics Reliability</i> , 2007, 47, 2114-2121.	0.9	16
146	Two-dimensional dopant imaging of silicon carbide devices by secondary electron potential contrast. <i>Microelectronic Engineering</i> , 2007, 84, 413-418.	1.1	14
147	Response of carbon nanotube transistors to electron beam exposure. <i>Microelectronic Engineering</i> , 2007, 84, 1596-1600.	1.1	9
148	Manufacturing and full characterization of silicon carbide-based multi-sensor micro-probes for biomedical applications. <i>Microelectronics Journal</i> , 2007, 38, 406-415.	1.1	50
149	Bidirectional current 4H-SiC VJFET. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 1544-1547.	0.8	1
150	Recent improvements of SiC micro-resonators. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 1548-1553.	0.8	4
151	Field-effect mobility temperature modeling of 4H-SiC metal-oxide-semiconductor transistors. <i>Journal of Applied Physics</i> , 2006, 100, 114508.	1.1	105
152	Numerical and Experimental Investigation on Bipolar Operation of 4H-SiC Normally-on Vertical JFETs. , 2006, , .		1
153	A field-effect electron mobility model for SiC MOSFETs including high density of traps at the interface. <i>Microelectronic Engineering</i> , 2006, 83, 440-445.	1.1	58
154	Ta ₂ Si short time thermal oxidized layers in N ₂ O and O ₂ to form high- k gate dielectric on SiC. <i>Applied Surface Science</i> , 2006, 253, 1741-1744.	3.1	2
155	A study of the influence of the annealing processes and interfaces with deposited SiO ₂ from tetra-ethoxy-silane for reducing the thermal budget in the gate definition of 4H-SiC devices. <i>Thin Solid Films</i> , 2006, 513, 248-252.	0.8	12
156	A SiC microdevice for the minimally invasive monitoring of ischemia in living tissues. <i>Biomedical Microdevices</i> , 2006, 8, 43-49.	1.4	23
157	Planar Edge Termination Design and Technology Considerations for 1.7-kV 4H-SiC PiN Diodes. <i>IEEE Transactions on Electron Devices</i> , 2005, 52, 2309-2316.	1.6	77
158	Characterisation and stabilisation of Pt/TaSi _x /SiO ₂ /SiC gas sensor. <i>Sensors and Actuators B: Chemical</i> , 2005, 109, 119-127.	4.0	10
159	Characterization of High- k Ta ₂ Si Oxidized Films on 4H-SiC and Si Substrates as Gate Insulator. <i>Journal of the Electrochemical Society</i> , 2005, 152, G259.	1.3	27
160	Ni/Ti ohmic and Schottky contacts on 4H-SiC formed with a single thermal treatment. <i>Diamond and Related Materials</i> , 2005, 14, 1146-1149.	1.8	40
161	Ta ₂ Si Thermal Oxidation: A Simple Route to a High- k Gate Dielectric on 4H-SiC. <i>Electrochemical and Solid-State Letters</i> , 2004, 7, F93.	2.2	6
162	Internal infrared laser deflection system: a tool for power device characterization. <i>Measurement Science and Technology</i> , 2004, 15, 1011-1018.	1.4	27

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163	A 4H-SiC high-power-density VJFET as controlled current limiter. IEEE Transactions on Industry Applications, 2003, 39, 1508-1513.	3.3	15
164	Accurate modeling and parameter extraction for 6H-SiC Schottky barrier diodes (SBDs) with nearly ideal breakdown voltage. IEEE Transactions on Electron Devices, 2001, 48, 2148-2153.	1.6	31
165	Montecarlo simulation of ion implantation into SiC-6H single crystal including channeling effect. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 46, 218-222.	1.7	22
166	Electro-thermal Simulation of a DC/DC Converter using a Relaxation Method. , 0, , .		6
167	Characterization of Nitrided Gate Oxide Formed by RTP for SiC MOSFET Application. Advanced Materials Research, 0, 324, 221-224.	0.3	1
168	High Temperature Capability of High Voltage 4H-SiC JBS. Materials Science Forum, 0, 711, 124-128.	0.3	2
169	Almost Free Standing Graphene on SiC(000-1) and SiC(11-20). Materials Science Forum, 0, 711, 235-241.	0.3	8
170	Design of Digital Electronics for High Temperature Using Basic Logic Gates Made of 4H-SiC MESFETs. Materials Science Forum, 0, 711, 104-108.	0.3	11
171	Integration of Temperature and Current Sensors in 4H-SiC VDMOS. Materials Science Forum, 0, 717-720, 1093-1096.	0.3	1
172	Gate Oxide Stability of 4H-SiC MOSFETs under On/Off-State Bias-Temperature Stress. Materials Science Forum, 0, 740-742, 553-556.	0.3	5
173	Remarkable Increase in Surge Current Capability of SiC Schottky Diodes Using Press Pack Contacts. Materials Science Forum, 0, 740-742, 873-876.	0.3	3
174	Edge Termination Design Improvements for 10 kV 4H-SiC Bipolar Diodes. Materials Science Forum, 0, 740-742, 609-612.	0.3	5
175	Study of 4H-SiC Schottky Diode Designs for 3.3kV Applications. Materials Science Forum, 0, 778-780, 795-799.	0.3	17
176	Formation of Graphene onto Atomically Flat 6H-SiC. Materials Science Forum, 0, 778-780, 1158-1161.	0.3	1
177	10 MeV Proton Irradiation Effect on 4H-SiC nMOSFET Electrical Parameters. Materials Science Forum, 0, 806, 121-125.	0.3	10
178	Low Energy Proton Radiation Impact on 4H-SiC nMOSFET Gate Oxide Stability. Materials Science Forum, 0, 778-780, 525-528.	0.3	3
179	Comparison of 5kV SiC JBS and PIN Diodes. Materials Science Forum, 0, 778-780, 867-870.	0.3	4
180	Rapid Thermal Oxidation of Si-Face N and P-Type On-Axis 4H-SiC. Materials Science Forum, 0, 778-780, 591-594.	0.3	1

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181	SiC Current Limiting FETs (CLFs) for DC Applications. Materials Science Forum, 0, 778-780, 895-898.	0.3	3
182	Study of Geometrical Effects in Charge Pumping Current for Lateral SiC nMOSFETs Electrical Characterization. Materials Science Forum, 0, 821-823, 717-720.	0.3	0
183	Cryogenic to High Temperature Exploration of 4H-SiC W-SBD. Materials Science Forum, 0, 821-823, 583-587.	0.3	0
184	Evidence of Channel Mobility Anisotropy on 4H-SiC MOSFETs with Low Interface Trap Density. Materials Science Forum, 0, 963, 473-478.	0.3	3
185	Fabrication and Characterization of Epitaxial Graphene Field Effect Transistor Devices Based on a Monolithic Bottom Gate. Materials Science Forum, 0, 1062, 603-607.	0.3	0
186	Edge Terminations for 4H-SiC Power Devices: A Critical Issue. Materials Science Forum, 0, 1062, 570-575.	0.3	2